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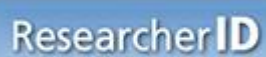
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原著論文 (9)

- [9] **Mian Wei***, Hai Jun Cho, and Hiromichi Ohta*, "Tuning of the optoelectronic properties for transparent oxide semiconductor ASnO_3 by modulating the size of A-ions", *ACS Appl. Electron. Mater.* **2**, 3971-3976 (2020). (December 8, 2020) (DOI: [10.1021/acsaelm.0c00806](https://doi.org/10.1021/acsaelm.0c00806))
- [8] **Mian Wei**#, Lizhikun Gong#, Dou-dou Liang#, Hai Jun Cho*, and Hiromichi Ohta*, "Fabrication and Operating Mechanism of Deep-UV Transparent Semiconducting SrSnO_3 -based Thin Film Transistor", *Adv. Electron. Mater.* **6**, 2000100 (2020). (June 15, 2020) (DOI: [10.1002/aelm.202000100](https://doi.org/10.1002/aelm.202000100)) (# Equally contributed to this work) [Press release](#)
- [7] Hai Jun Cho,* Koichi Sato, **Mian Wei**, Gowoon Kim, and Hiromichi Ohta*, "Effect of lattice distortions on the electron and thermal transport properties of transparent oxide semiconductor $\text{Ba}_{1-x}\text{Sr}_x\text{SnO}_3$ solid solution films", *J. Appl. Phys.* **127**, 115701 (2020). (March 17, 2020) (DOI: [10.1063/5.0002172](https://doi.org/10.1063/5.0002172)) [Editors' pick](#)
- [6] **Mian Wei**, Anup Sanchela, Bin Feng, Yuichi Ikuhara, Hai Jun Cho*, and Hiromichi Ohta*, "High electrical conducting deep-ultraviolet-transparent oxide semiconductor La-doped SrSnO_3 exceeding $\sim 3000 \text{ S cm}^{-1}$ ", *Appl. Phys. Lett.* **116**, 022103 (2020). (January 13th, 2020) (DOI: [10.1063/1.5128410](https://doi.org/10.1063/1.5128410))
- [5] Hai Jun Cho*, Bin Feng, Takaki Onozato, **Mian Wei**, Anup Sanchela, Yuichi Ikuhara, and Hiromichi Ohta*, "Investigation of electrical and thermal transport property reductions in La-doped BaSnO_3 films", *Phys. Rev. Materials* **3**, 094601 (2019). (September 3rd, 2019) (DOI: [10.1103/PhysRevMaterials.3.094601](https://doi.org/10.1103/PhysRevMaterials.3.094601)) [Editors' Suggestion](#)
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- [3] Anup V. Sanchela*, **Mian Wei**, Hai Jun Cho, and Hiromichi Ohta*, "Thermopower modulation clarification of the operating mechanism in wide bandgap

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[2] Hai Jun Cho*, Takaki Onozato, **Mian Wei**, Anup Sanchela, and Hiromichi Ohta*, "Effects of vacuum annealing on the electron mobility of epitaxial La-doped BaSnO₃ films", *APL Mater.* **7**, 022507 (2019). (DOI: [10.1063/1.5054154](https://doi.org/10.1063/1.5054154))

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[14] **Mian Wei**, Hai Jun Cho, and Hiromichi Ohta, "Tuning of the Optoelectronic Properties for Transparent Oxide Semiconductor ASnO₃ by Modulating the Size of A-ions (21-3507)", The 8th International Congress on Ceramics (ICC8), Virtual, April 25-30, 2021.

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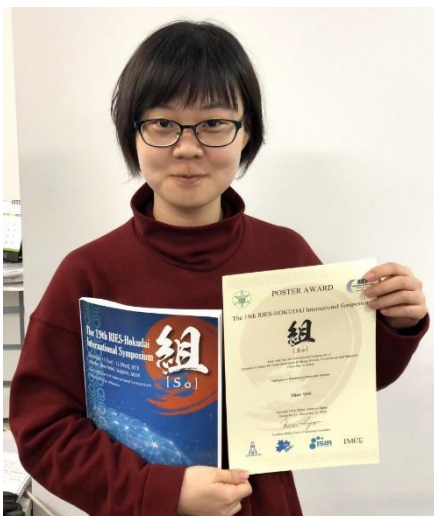
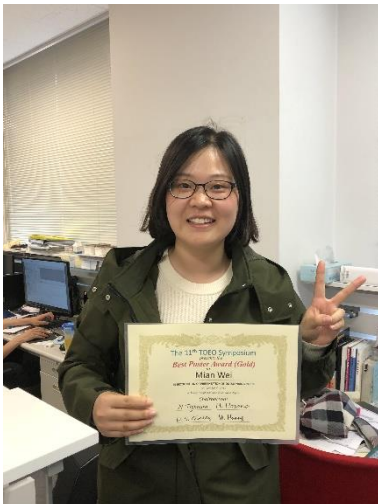
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- [11] **Mian Wei**, Anup V. Sanchela, Bin Feng, Yuichi Ikuhara, Hai Jun Cho, and Hiromichi Ohta, "New Deep-Ultraviolet Transparent Oxide Semiconductor, La-doped SrSnO₃", The 3rd Workshop on Functional Materials Science, Sapporo, Japan, December 18th-20th, 2019. (Poster)
- [10] **Mian Wei**, Anup V. Sanchela, Hai Jun Cho, and Hiromichi Ohta, "High electrical conductivity exceeding ~3000 S cm⁻¹ of a transparent oxide semiconductor, La-doped SrSnO₃", Materials Research Meeting 2019, Yokohama, Japan, December 10-14, 2019
- [9] **Mian Wei**, Anup V. Sanchela, Bin Feng, Yuichi Ikuhara, Hai Jun Cho, and Hiromichi Ohta, "Epitaxial film growth of a deep-ultraviolet transparent oxide semiconductor, La-doped SrSnO₃", RIES-NCTU Workshop, Hokkaido University, Sapporo, Japan, December 3-4, 2019. (Poster)
- [8] **Mian Wei**, Anup V. Sanchela, Bin Feng, Yuichi Ikuhara, Hai Jun Cho, and Hiromichi Ohta, "Epitaxial film growth of a deep-ultraviolet transparent oxide semiconductor, La-doped SrSnO₃", The 20th RIES-HOKUDAI International Symposium, Hokkaido University, Sapporo, Japan, December 2-3, 2019. (Poster)
- [7] **Mian Wei**, Anup V. Sanchela, Bin Feng, Yuichi Ikuhara, Hai Jun Cho, and Hiromichi Ohta, "New Deep-Ultraviolet Transparent Oxide Semiconductor, La-doped SrSnO₃", TOEO-11, Nara, Japan, October 7-9, 2019 **Best Poster Award (Gold)**
- [6] **魏 冕**, Anup Sanchela, 馮 斌, 幾原雄一, Hai Jun Cho, 太田裕道, "3000 S cm⁻¹を超える高導電性深紫外透明酸化物半導体 Laドーピング SrSnO₃", 2019年 第80回応用物理学会秋季学術講演会, 北海道大学 札幌キャンパス, 北海道札幌市, 2019年9月18日-21日.
- [5] **Mian Wei**, Anup V. Sanchela, Hai Jun Cho, Hiromichi Ohta, "Thermopower analysis of effective mass in a transparent oxide semiconductor, La-doped SrSnO₃", The 19th RIES-HOKUDAI International Symposium 組[So], Jozankei View Hotel, Sapporo, December 11th-12th, 2018 (Poster) **Poster Award**
- [4] **M. Wei**, A. Sanchela, J. Lee, G. Kim, H. Jeon, B. Feng, Y. Ikuhara, H. Cho, and H. Ohta, "Electron mobility improvement of La-doped BaSnO₃ films grown under the ozone atmosphere", The 2nd Workshop on Functional Materials Science, Busan, South Korea, October 22-23, 2018
- [3] **M. Wei**, A. Sanchela, J. Lee, G. Kim, H. Jeon, B. Feng, Y. Ikuhara, H. Cho and H. Ohta, "A perverse transparent oxide semiconductor, La:BaSnO₃", 2018年 第79回 応用物理学会秋季学術講演会, 名古屋国際会議場 (名古屋・愛知), 2018年9月18日-21日

[2] **Mian Wei**, Anup V. Sanchela, Bin Feng, Joonhyuk Lee, Gowoon Kim, Hyoungjeen Jeen, Yuichi Ikuhara, and Hiromichi Ohta, "Origin of Mobility Suppression in La-doped BaSnO₃ Films (II)", 2018 年 第 65 回応用物理学会春季学術講演会, Waseda University (Tokyo), 17-20 March, 2018 (Domestic)

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受賞 (3)



[3] Best Poster Award (Gold) at 11th International Symposium on Transparent Oxide and Related Materials for Electronics and Optics (TOEO-11) (October 9th, 2019). “New Deep-Ultraviolet Transparent Oxide Semiconductor, La-doped SrSnO₃”, **Mian Wei***, Anup Sanchela, Bin Feng, Yuichi Ikuhara, Hai Jun Cho, and Hiromichi Ohta [賞状](#) [写真](#)

[2] Poster Award for the Presentation in The 19th RIES-Hokudai International Symposium. (December 12th, 2018) **Mian Wei**, Anup V. Sanchela, Hai Jun Cho, Hiromichi Ohta, “Thermopower analysis of effective mass in a transparent oxide semiconductor, La-doped SrSnO₃”, The 19th RIES-HOKUDAI International Symposium 組[So], Jozankei View Hotel, Sapporo, December 11th-12th, 2018 (Poster) [賞状](#)

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報道 (3)

[1] OPTRONICS ONLINE, “北大, DUV を透過する透明トランジスタを実現” (2020.6.16)

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